

FC8V33030L

Dual N-channel MOSFET

For DC-DC Converter

■ Features

- Low drain-source ON resistance: $R_{DS(on)}$ typ. = 22 m Ω (V_{GS} = 4.5 V)
 - High-speed switching : Q_g = 3.8 nC
 - Halogen-free / RoHS compliant
- (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol:6A

■ Basic Part Number

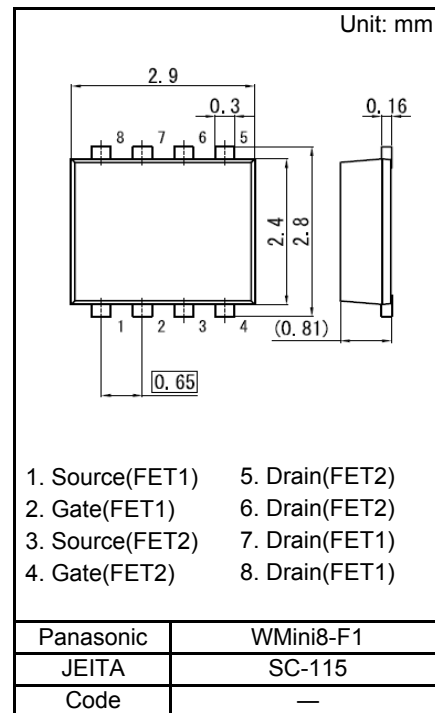
Dual Nch MOS 33 V (Individual)

■ Packaging

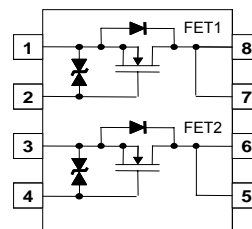
FC8V33030L Embossed type (Thermo-compression sealing):
3 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25\text{ }^{\circ}\text{C}$

| Parameter | | Symbol | Rating | Unit |
|--------------|---|------------------|-------------|------|
| FET1 FET2 | Drain-source Voltage | V_{DS} | 33 | V |
| | Gate-source Voltage | V_{GS} | ± 20 | V |
| | Drain Current (Steady State) ^{*1} | I_D | 6.5 | A |
| | Drain Current ($t=10\text{s}$) ^{*1} | | 8 | |
| | Drain Current (Pulsed) ^{*1,2} | I_{Dp} | 26 | |
| | Source Current (Pulsed) (Body Diode) ^{*1,2} | I_{Sp} (BD) | 6.5 | |
| Overall | Power Dissipation (Steady State) ^{*1} | P_D | 1 | W |
| | Power Dissipation ($t=10\text{s}$) ^{*1} | | 1.5 | |
| | Channel Temperature | T_{ch} | 150 | |
| | Storage Temperature Range | T_{stg} | -55 to +150 | |

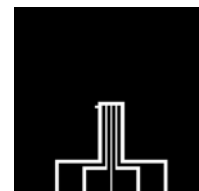
Note: ^{*1} Device mounted on a glass-epoxy board (See Figure 1)^{*2} Pulse test: Ensure that the channel temperature does not exceed 150 $^{\circ}\text{C}$.

Internal Connection



Pin name

1. Source(FET1) 5. Drain(FET2)
2. Gate(FET1) 6. Drain(FET2)
3. Source(FET2) 7. Drain(FET1)
4. Gate(FET2) 8. Drain(FET1)



FR-4 (Unit: mm)
25.4 x 25.4 x 0.8

(Figure 1) Glass-Epoxy Board

■ Electrical Characteristics $T_a = 25\text{ }^{\circ}\text{C} \pm 3\text{ }^{\circ}\text{C}$

Static Characteristics

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Unit |
|-------------------------------------|----------|-----------------------------|------|------|----------|---------------|
| Drain-source Breakdown Voltage | VDSS | ID = 1 mA, VGS = 0 V | 33 | | | V |
| Zero Gate Voltage Drain Current | IDSS | VDS = 33 V, VGS = 0 V | | | 10 | μA |
| Gate-source Leakage Current | IGSS | VGS = ± 16 V, VDS = 0 V | | | ± 10 | μA |
| Gate-source Threshold Voltage | Vth | ID = 0.48 mA, VDS = 10 V | 1 | | 2.5 | V |
| Drain-source On-state Resistance *1 | RDS(on)1 | ID = 3.3 A, VGS = 10 V | | 15 | 20 | m Ω |
| | RDS(on)2 | ID = 3.3 A, VGS = 4.5 V | | 22 | 35 | |

Note *1 Pulse test: Ensure that the channel temperature does not exceed 150 $^{\circ}\text{C}$

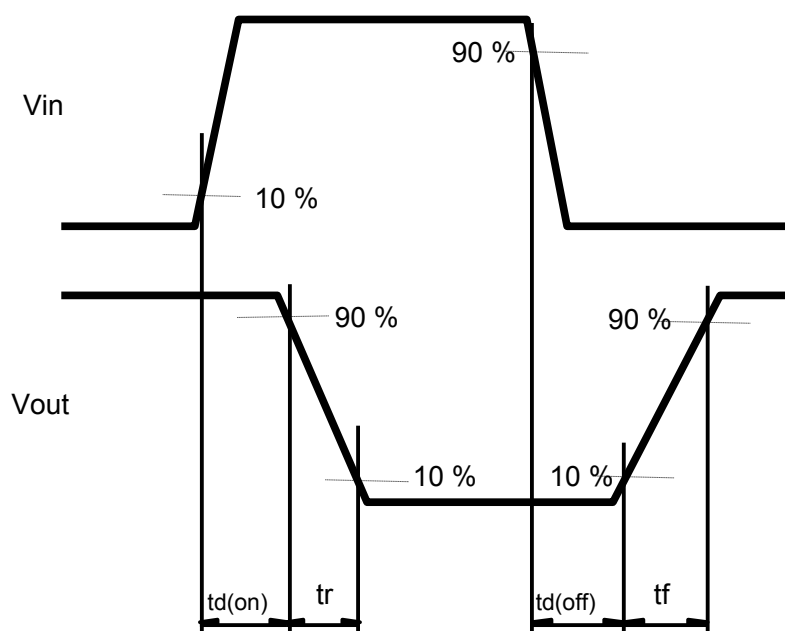
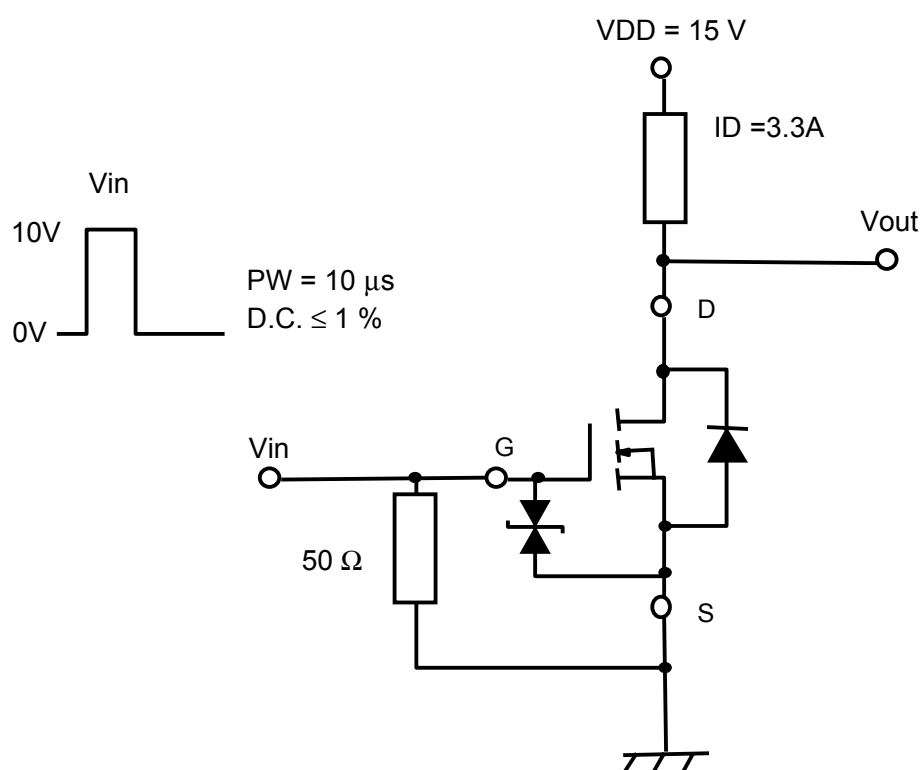
Dynamic Characteristics

| | | | | | | |
|------------------------------|---------|---|--|-----|--|----|
| Input Capacitance | Ciss | VDS = 10 V, VGS = 0 V, f = 1 MHz | | 360 | | pF |
| Output Capacitance | Coss | | | 70 | | |
| Reverse Transfer Capacitance | Crss | | | 50 | | |
| Turn-On Delay Time | td(on) | VDD = 15 V, VGS = 0 to 10 V | | 8 | | ns |
| Rise Time | tr | ID = 3.3 A (Figure 2) | | 3 | | |
| Turn-Off Delay Time | td(off) | VDD = 15 V, VGS = 10 to 0 V | | 24 | | |
| Fall Time | tf | ID = 3.3 A (Figure 2) | | 9 | | |
| Total Gate Charge | Qg | VDD = 15 V, VGS = 0 to 4.5 V, ID = 6.5 A | | 3.8 | | nC |
| Gate-source Charge | Qgs | | | 1.4 | | |
| Gate-drain Charge | Qgd | | | 1.6 | | |

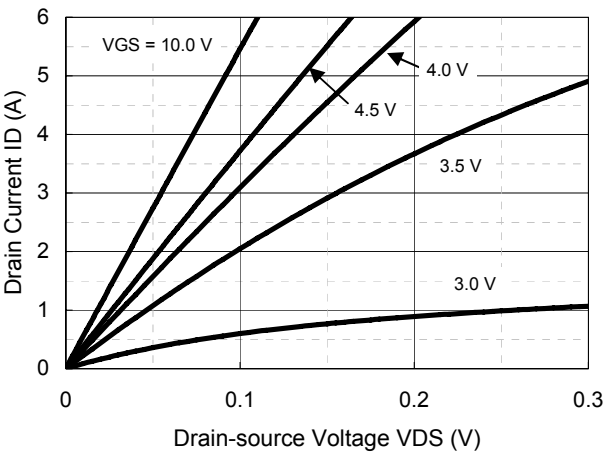
Body Diode Characteristic

| | | | | | | |
|--------------------------|-----|-----------------------|--|-----|-----|---|
| Diode Forward Voltage *1 | VSD | IS = 3.3 A, VGS = 0 V | | 0.8 | 1.2 | V |
|--------------------------|-----|-----------------------|--|-----|-----|---|

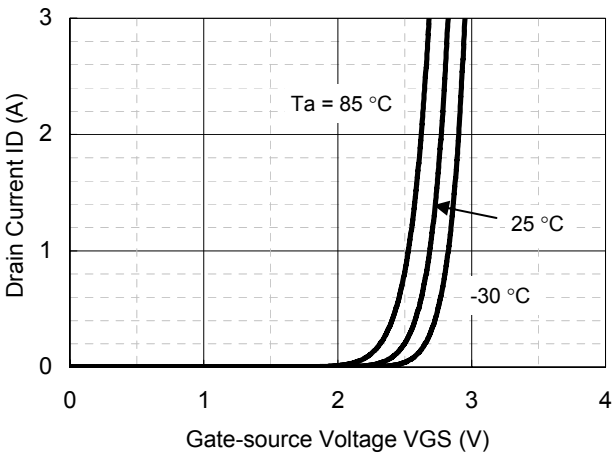
Note *1 Pulse test: Ensure that the channel temperature does not exceed 150 $^{\circ}\text{C}$



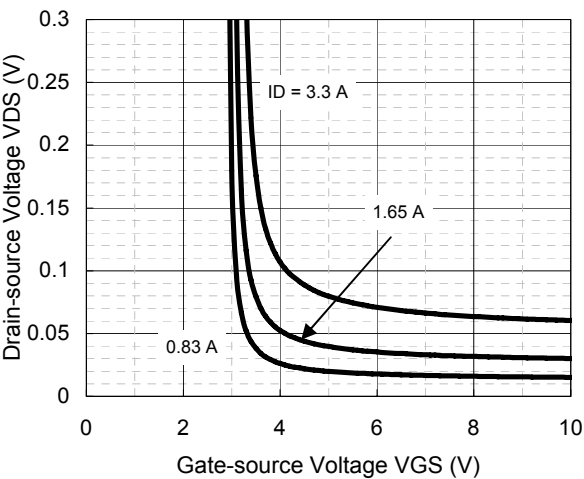
(Figure 2) Measurement circuit for Turn-On Delay Time/Rise Time/Turn-Off Delay Time/Fall Time



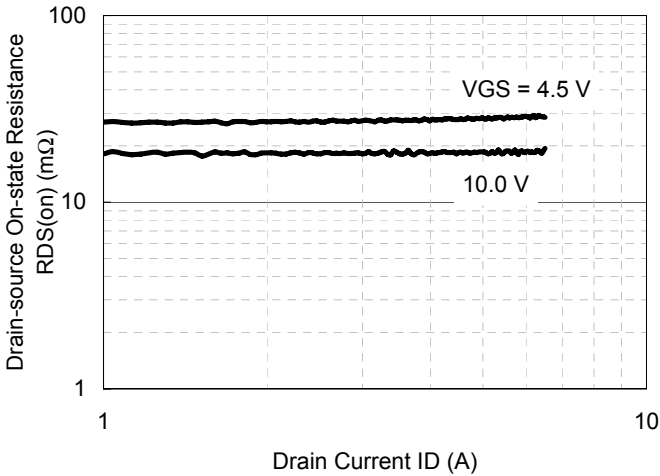
ID - VDS



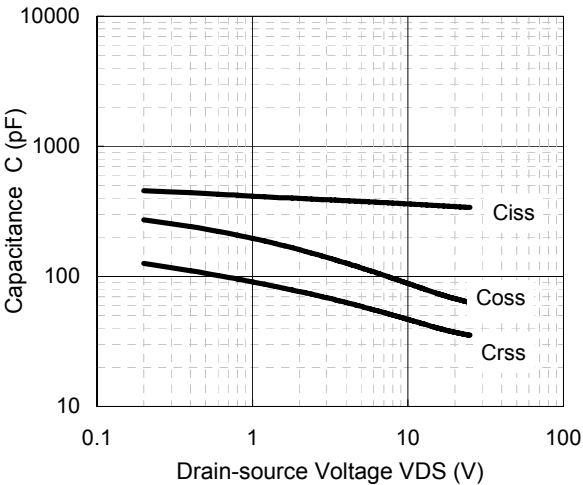
ID - VGS



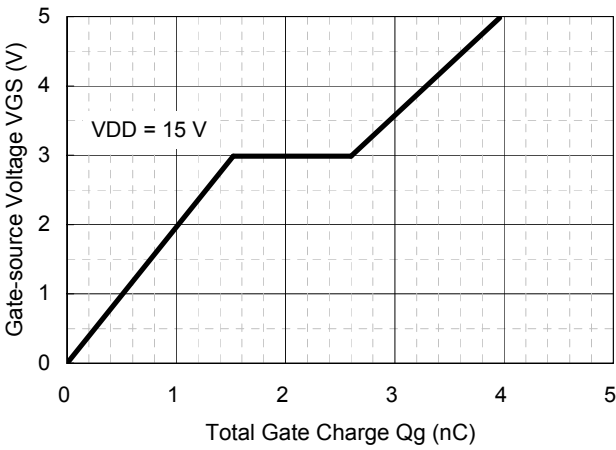
VDS - VGS



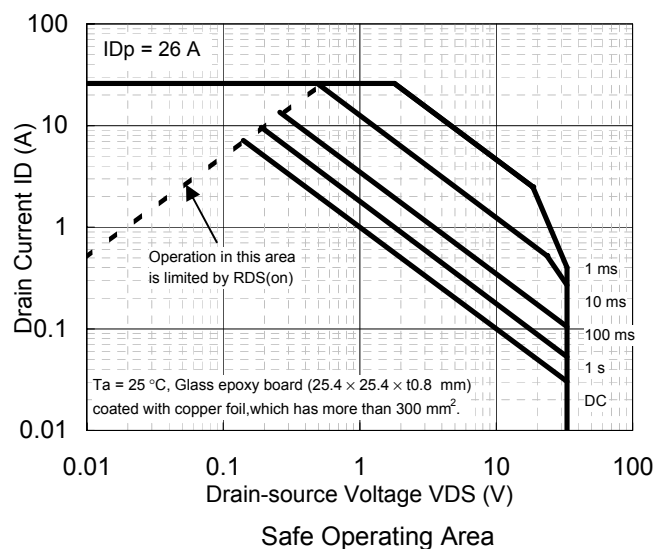
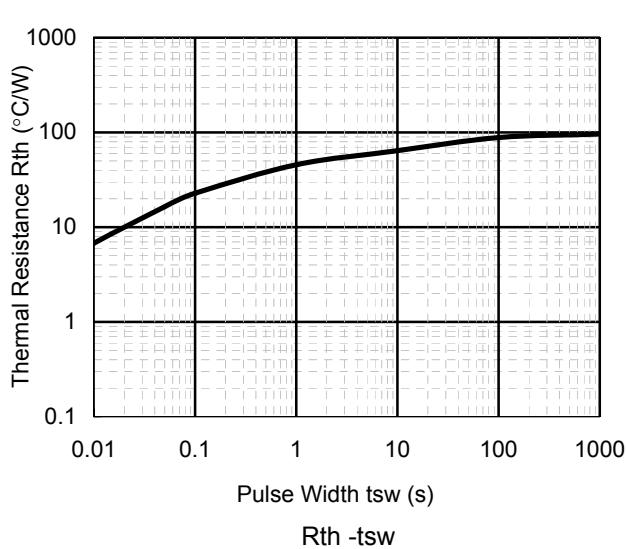
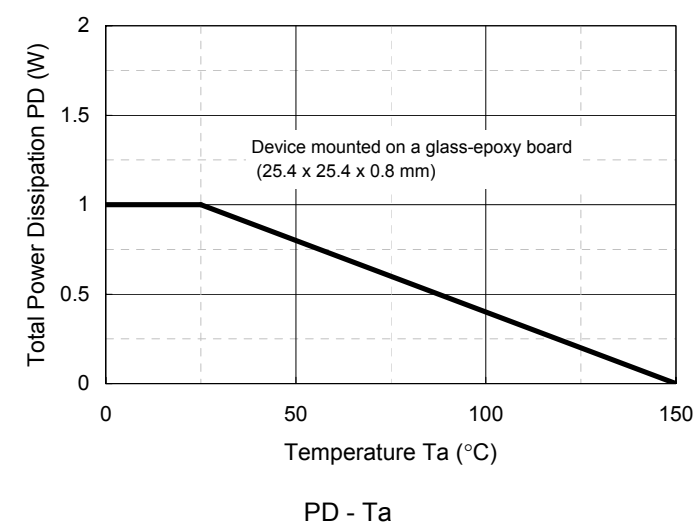
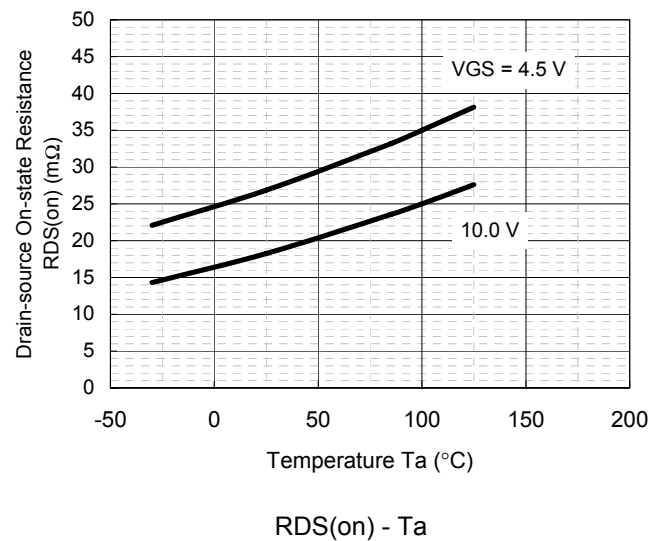
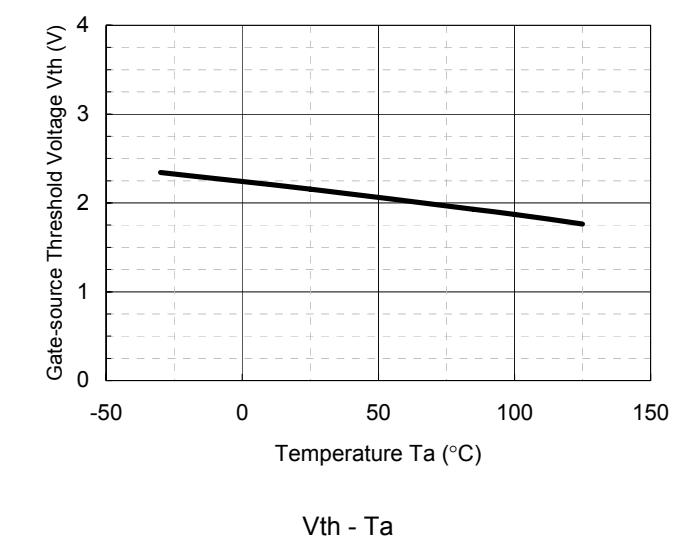
RDS(on) - ID



Capacitance - VDS

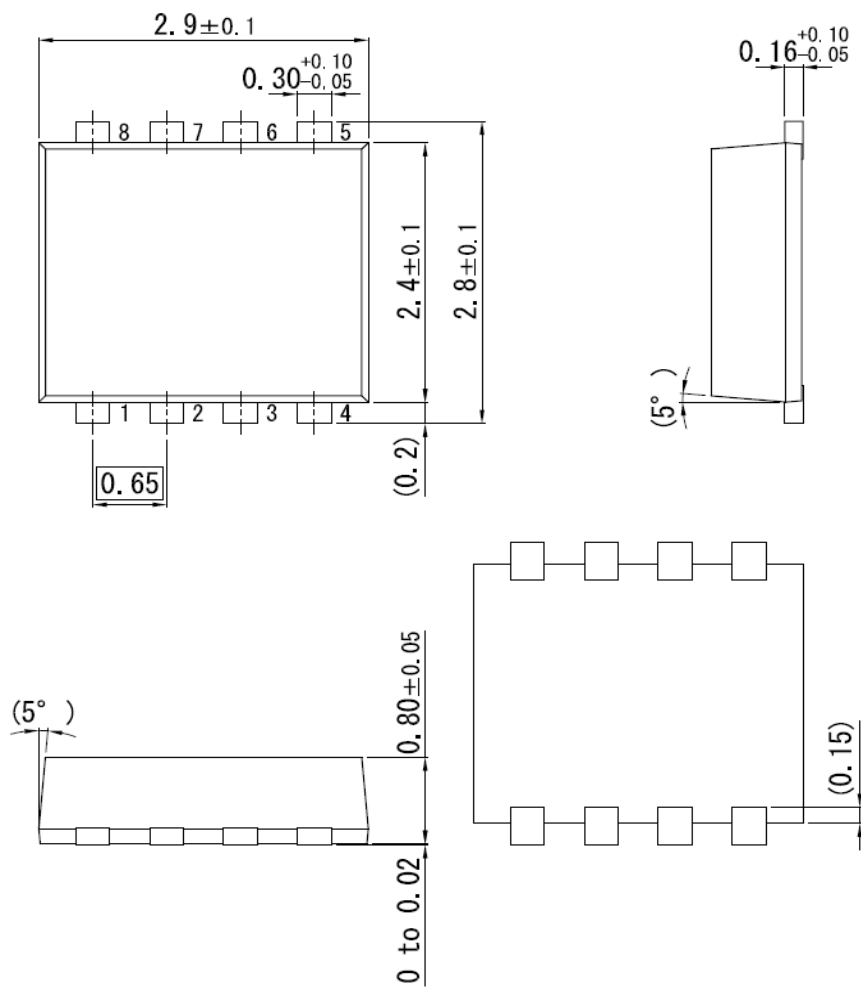


Dynamic Input/Output Characteristics

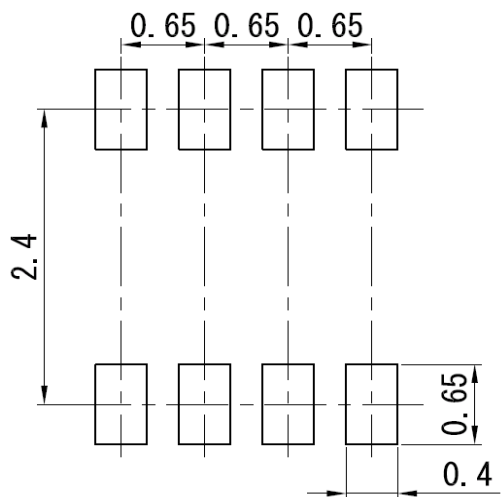


WMini8-F1

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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